MOS FET

### FC4B22270L1

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### Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

#### ■ Features

- Low source-source ON resistance:Rss(on) typ. = 18 m $\Omega$ (VGS = 3.8 V)
- · CSP(Chip Size Package)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1)

■ Marking Symbol: 2J

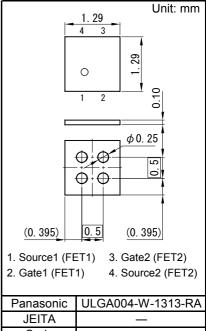
### ■ Packaging

Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

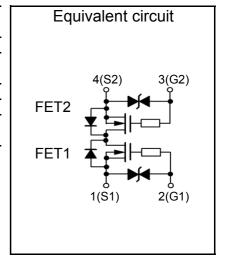
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit	
Source-source Voltage	VSS	20	V	
Gate-source Voltage	VGS	±12	V	
Source Current (DC)	IS *1	4	A	
	IS *2	8		
Source Current (Pulsed)	ISp *2	40	Α	
Total Power Dissipation	PD *1	0.37	W	
Total i owel Dissipation	PD *2	1.5		
Channel Temperature	Tch	150	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	
Thermal Resistance (ch-a)	Rth *1	338	°C/W	
	Rth *2	83		

- \*1 Mounted on FR4 board (25.4 mm  $\times$  25.4 mm  $\times$  t1.0 mm) Note using the minimum recommended pad size (36µm Copper ).
  - \*2 Mounted on Ceramic substrate (70 mm  $\times$  70 mm  $\times$  t1.0 mm).
  - \*3  $t = 10 \mu s$ , Duty Cycle  $\leq 1 \%$



ULGA004-W-1313-RA



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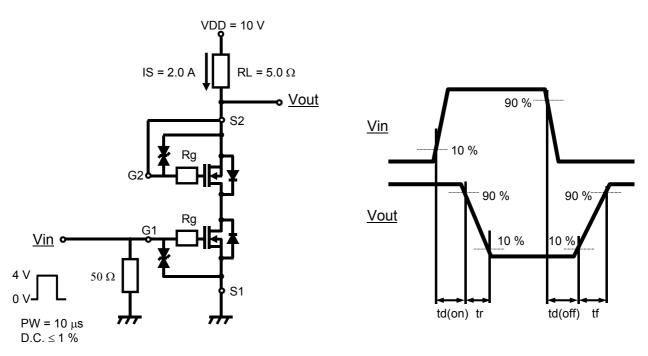
### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μΑ
Gate-source Leakage Current	IGSS	VGS = ±8 V, VSS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	IS = 0.31 mA, VSS = 10 V	0.35	0.90	1.4	V
Source-source On-state Resistance	RSS(on)1	IS = 2.0 A, VGS = 4.5 V	12	17	22	mΩ
	RSS(on)2	IS = 2.0 A, VGS = 3.8 V	12.5	18	23	
	RSS(on)3	IS = 2.0 A, VGS = 3.1 V	13.5	19	26.5	
	RSS(on)4	IS = 2.0 A, VGS = 2.5 V	14	22	37	
Body Diode Forward Voltage	VF(s-s)	IF = 2.0 A, VGS = 0 V		0.8	1.2	V
Input Capacitance *1	Ciss			910		
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 KHz		105		pF
Reverse Transfer Capacitance *1	Crss			80		
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.25		0
Rise Time *1,*2	tr	IS = 2.0 A		0.55		μS
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		1.65		0
Fall Time *1,*2	tf	IS = 2.0 A		1.0		μS
Total Gate Charge *1	Qg	VDD = 10 V		9		
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V,		2.6		nC
Gate-drain Charge *1	Qgd	IS = 2.0 A		2.4		

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- \*1 Guaranteed by design, not subject to production testing
- \*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

#### Note2:Measurement circuit

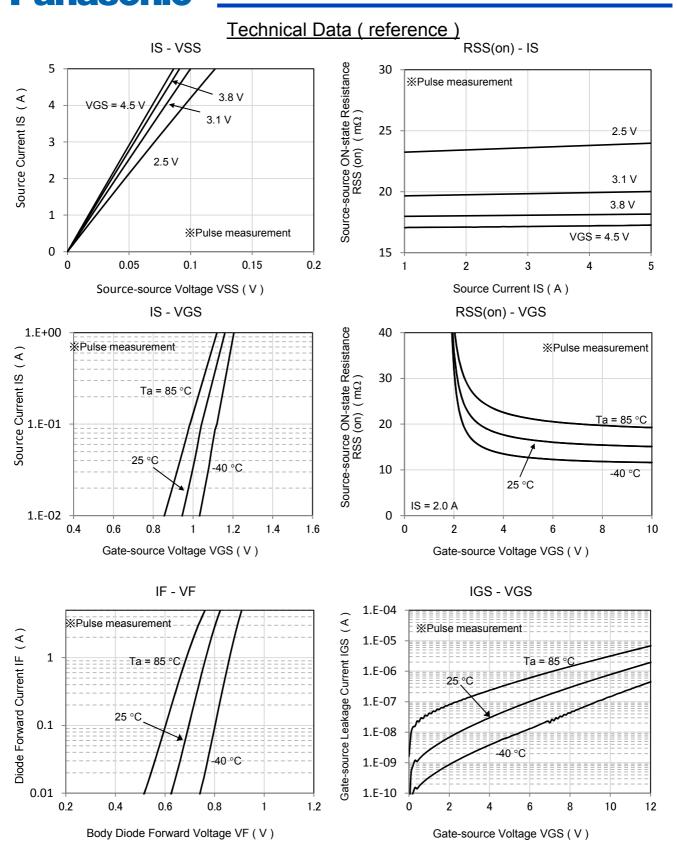


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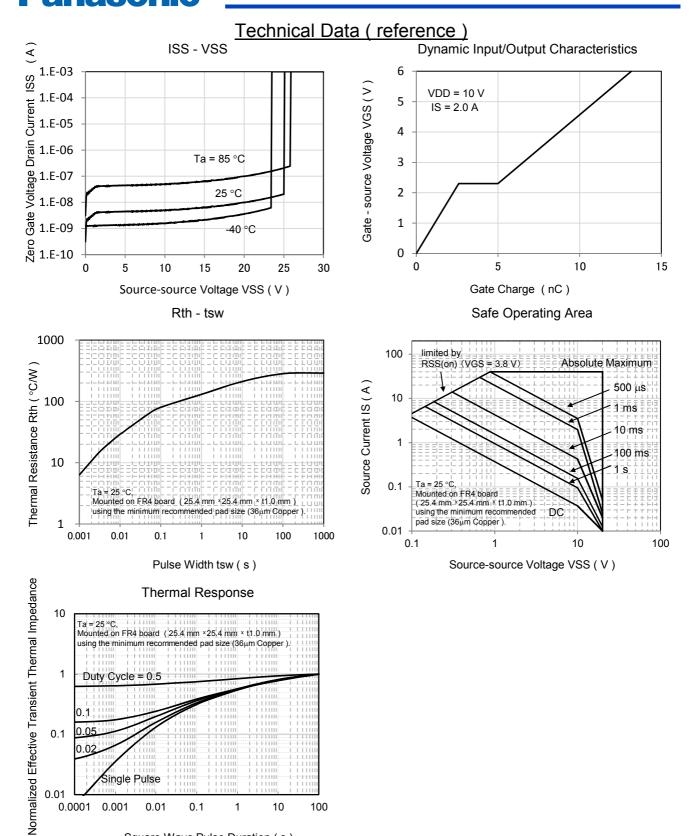
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0.0001 0.001

0.01

0.1

Square Wave Pulse Duration (s)

10

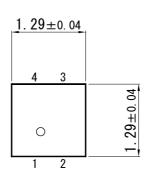
100

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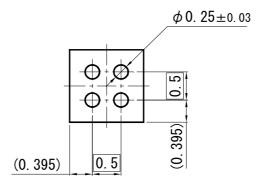
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■ Outline (ULGA004-W-1313-RA)

Unit: mm

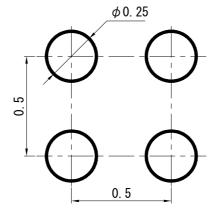






■ Land Pattern (Reference)

Unit: mm



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